

58th Meeting of the INTC

Production of phosphorus-vacancy centers in diamond for optical and spin characterization

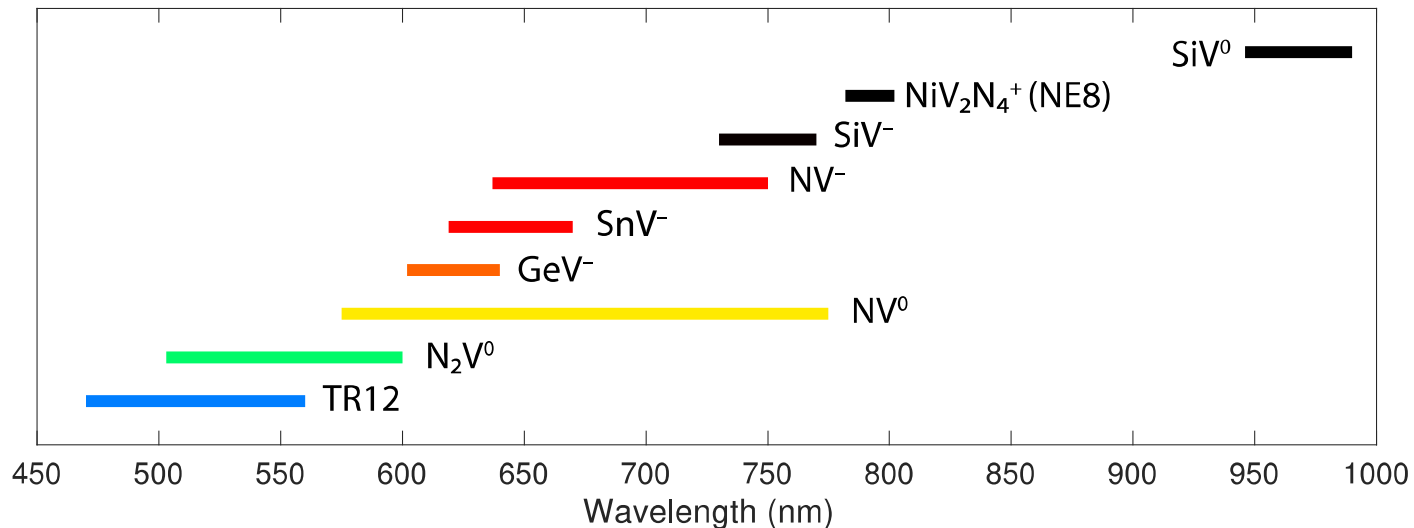
B. L. Green,¹ M. E. Newton,¹ and K. Johnston²

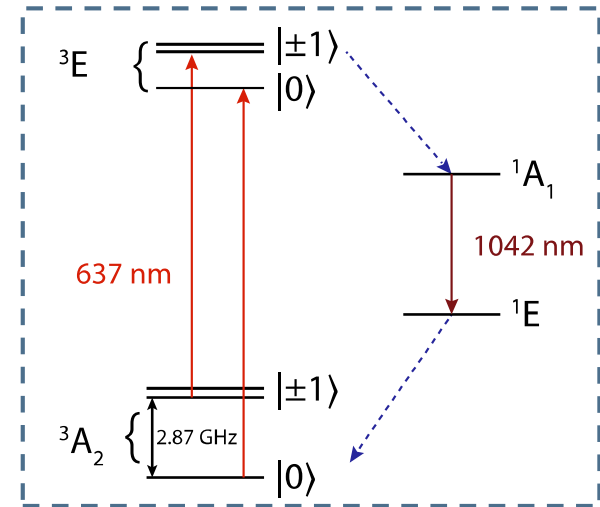
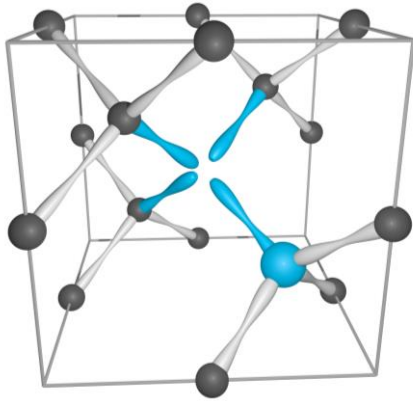
¹*Department of Physics, University of Warwick, Coventry CV4 7AL, United Kingdom*

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Single emitters in diamond

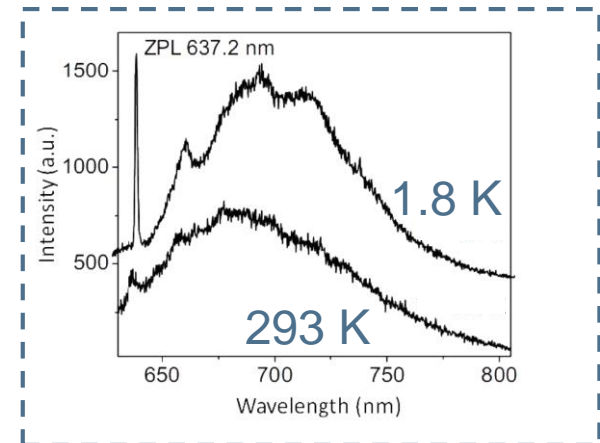
- ▶ Diamond is an ideal host matrix for functional point defects with optically-accessible quantum properties:
 - high Debye temperature
 - low spin-density
 - large band gap → broadband optical transparency (220 – 2400 nm)





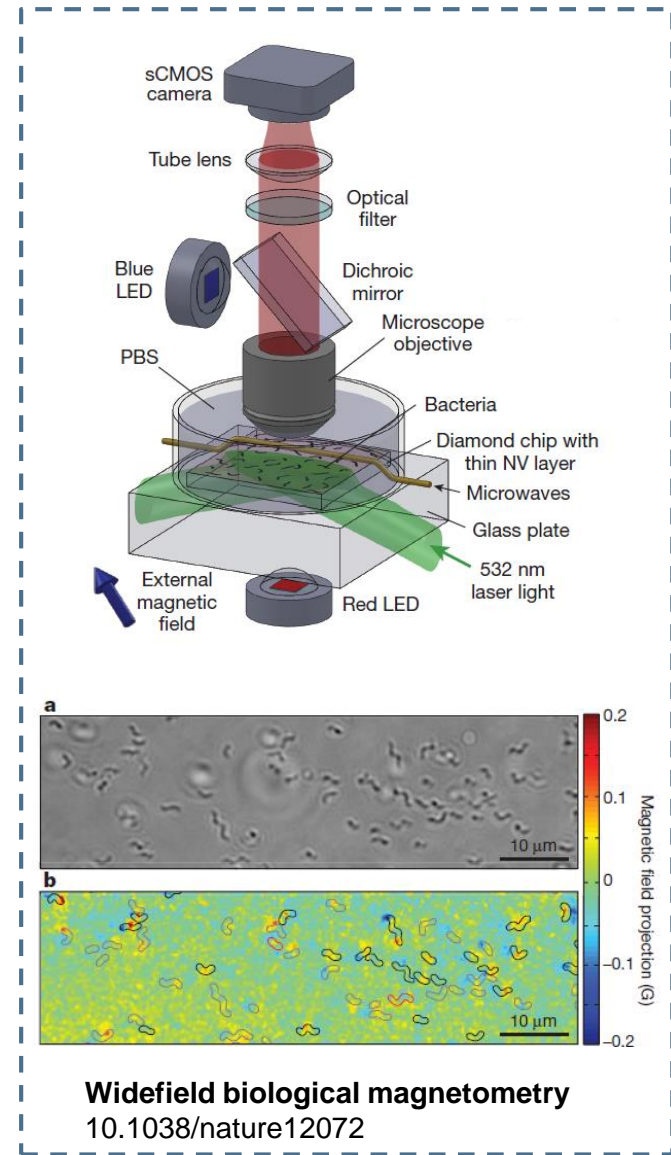
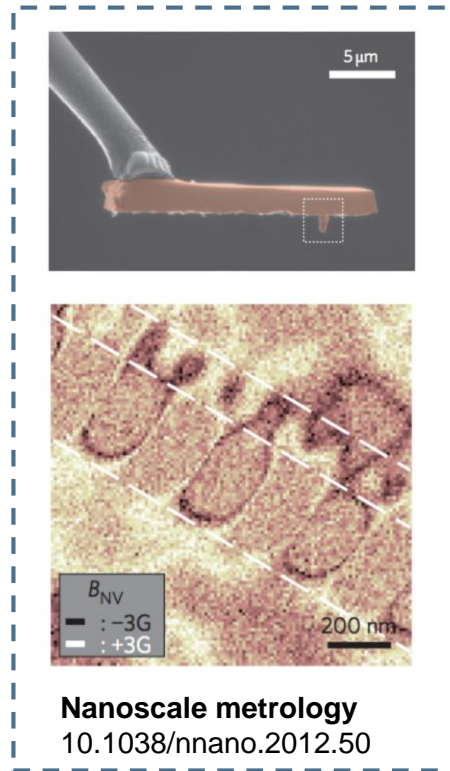
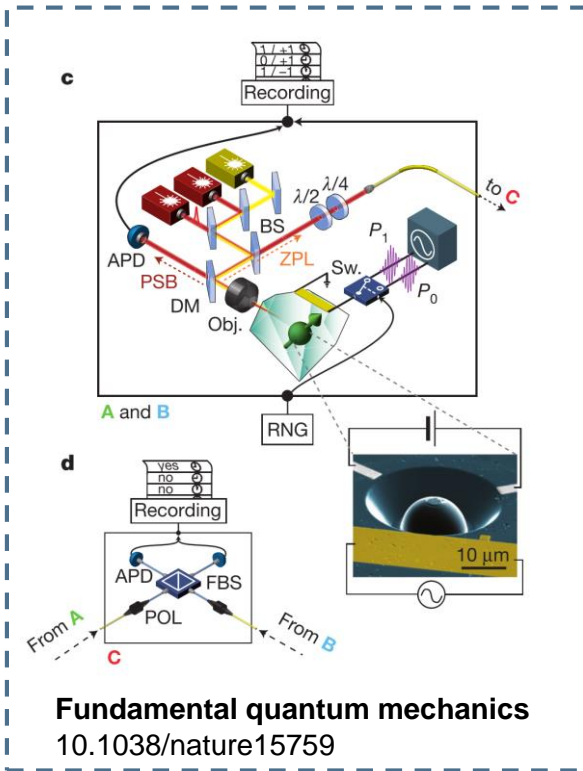
NV⁻

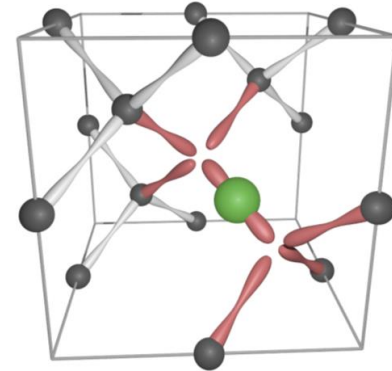
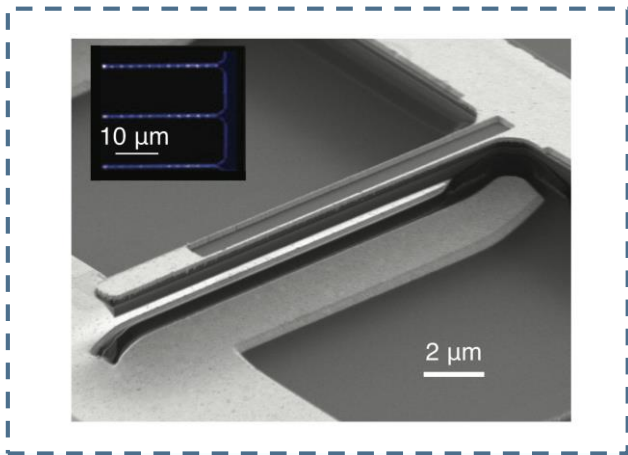
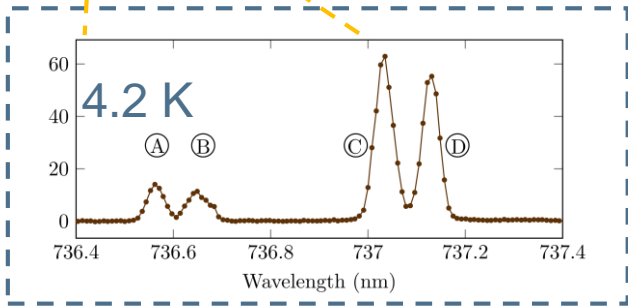
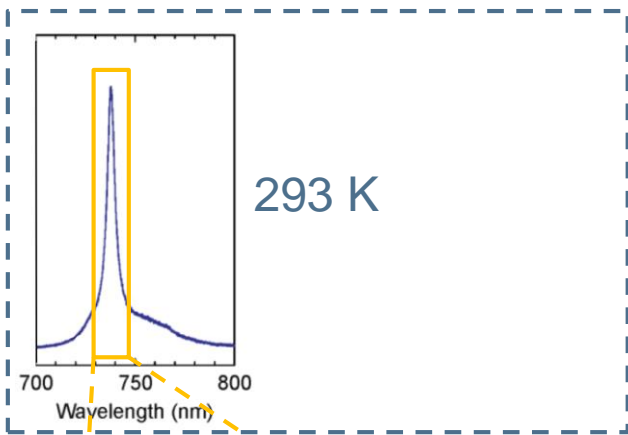
- ✓ Fast optical spin initialization
- ✓ High fidelity optical spin readout at room temperature
- ✓ Long coherence times
- ✗ Broadband emission
- ✗ Sensitive to strain



NV—

- ▶ Now a well-understood system
- ▶ Applications include:



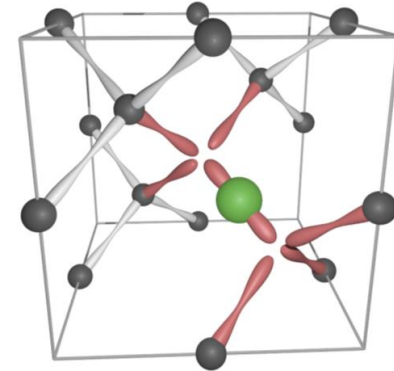
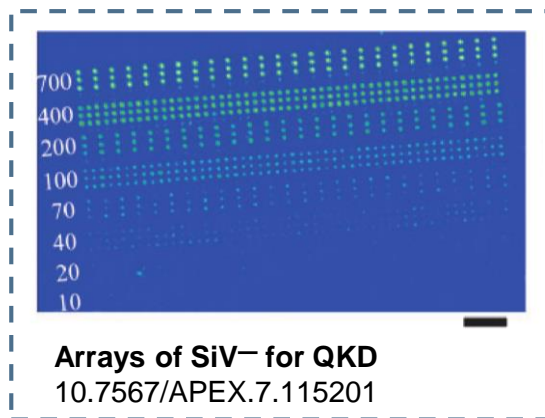
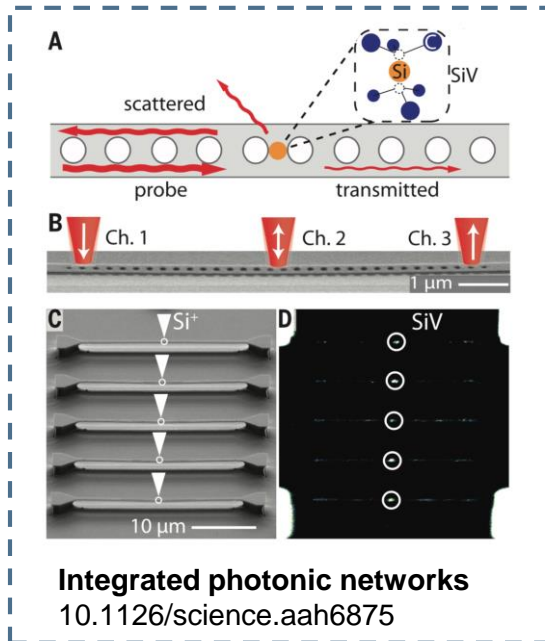


SiV⁻

- X Slow spin initialization
- X Slow spin readout (and only at 4 K or lower)
- X Short coherence at >100 mK
- ✓ Narrowband emission
- ✓ Tuneable ZPL



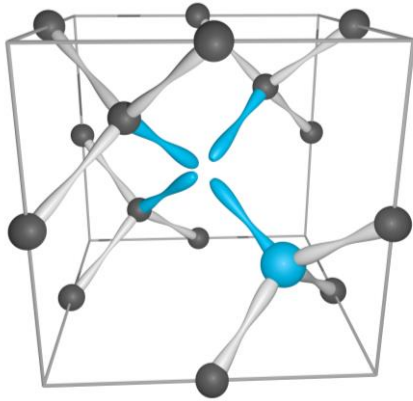
► Applications primarily photonic



SiIV-

- X Slow spin initialization
- X Slow spin readout (and only at 4 K or lower)
- X Short coherence at >100 mK
- ✓ Narrowband emission
- ✓ Tuneable ZPL

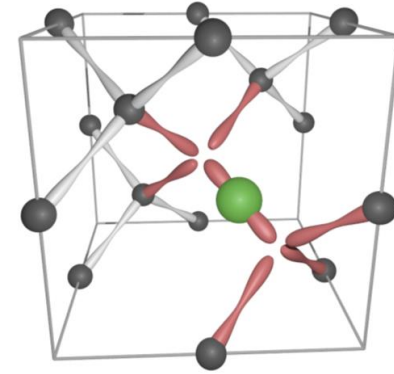




NV⁻

- ✓ Fast optical spin initialization
- ✓ High fidelity optical spin readout at room temperature
- ✓ Long coherence times

- ✗ Broadband emission
- ✗ Sensitive to strain



SiV⁻

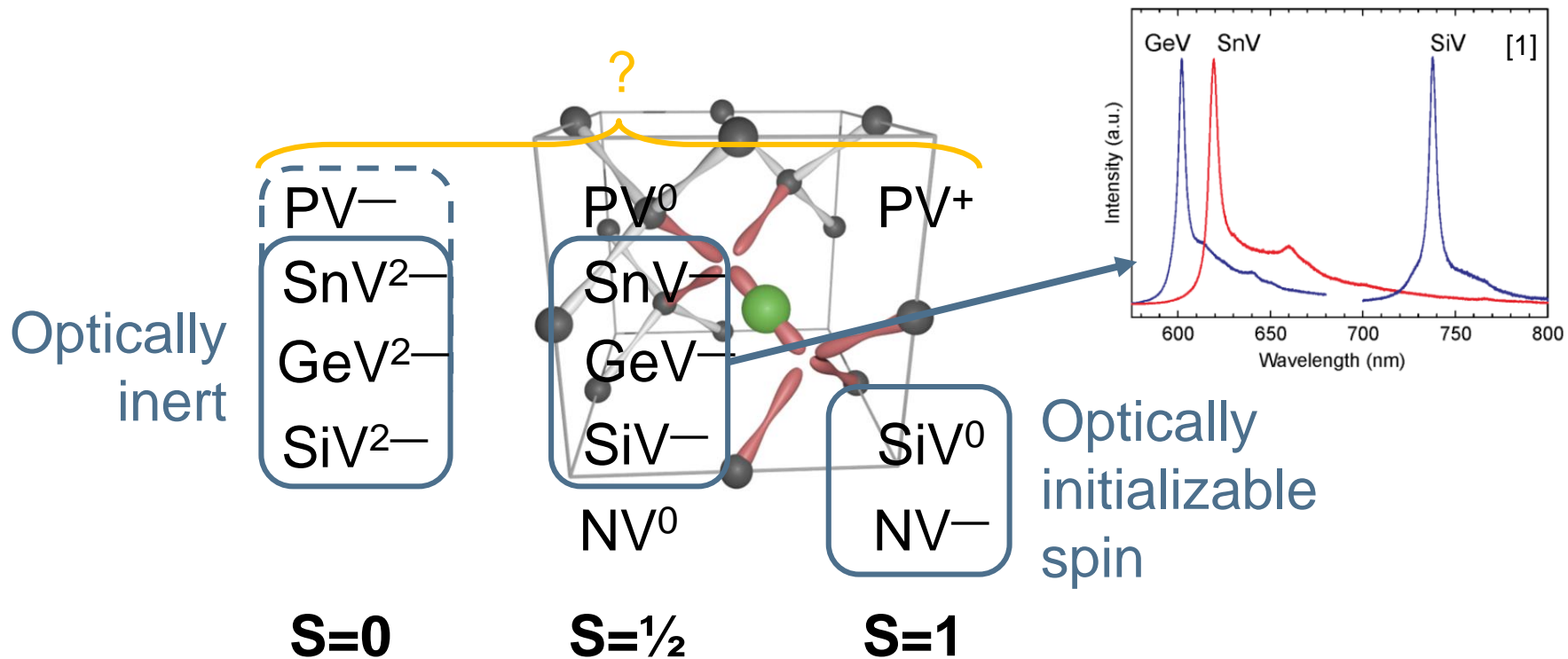
- ✗ Slow spin initialization
- ✗ Slow spin readout (and only at 4 K or lower)
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- ✓ Narrowband emission
- ✓ Tuneable ZPL

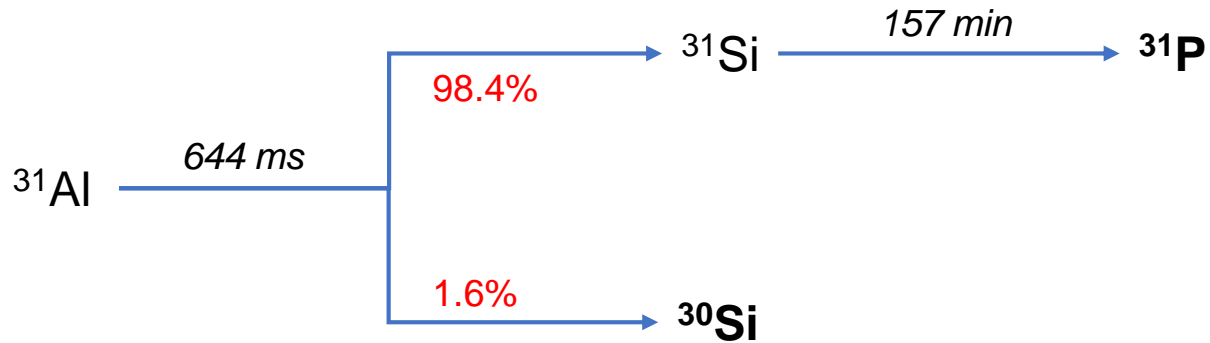


Single emitters in diamond

- ▶ Significant similarities between different “vacancy-cage” optical emitters



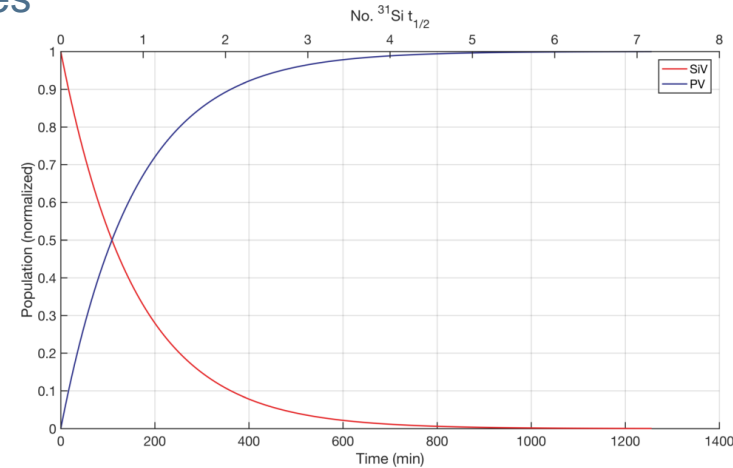
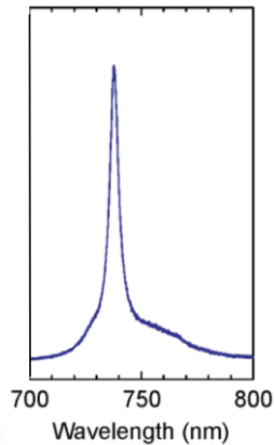
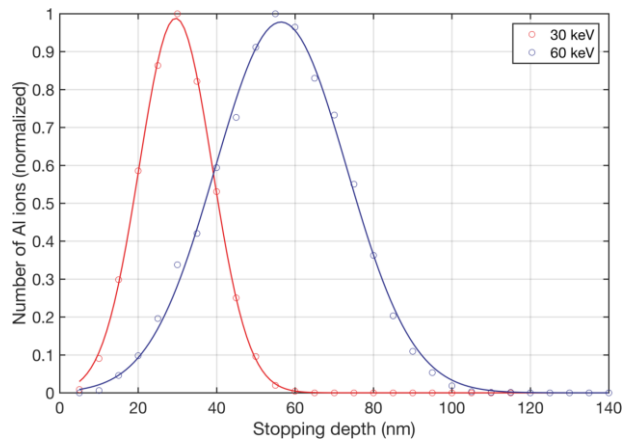
Production at ISOLDE



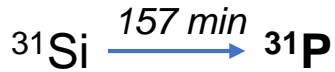
Implant at ~50 keV

→ Anneal to form ^{31}SiV
>800°C to mobilize vacancies

→ Monitor decay of SiV
Look for PV spectrum



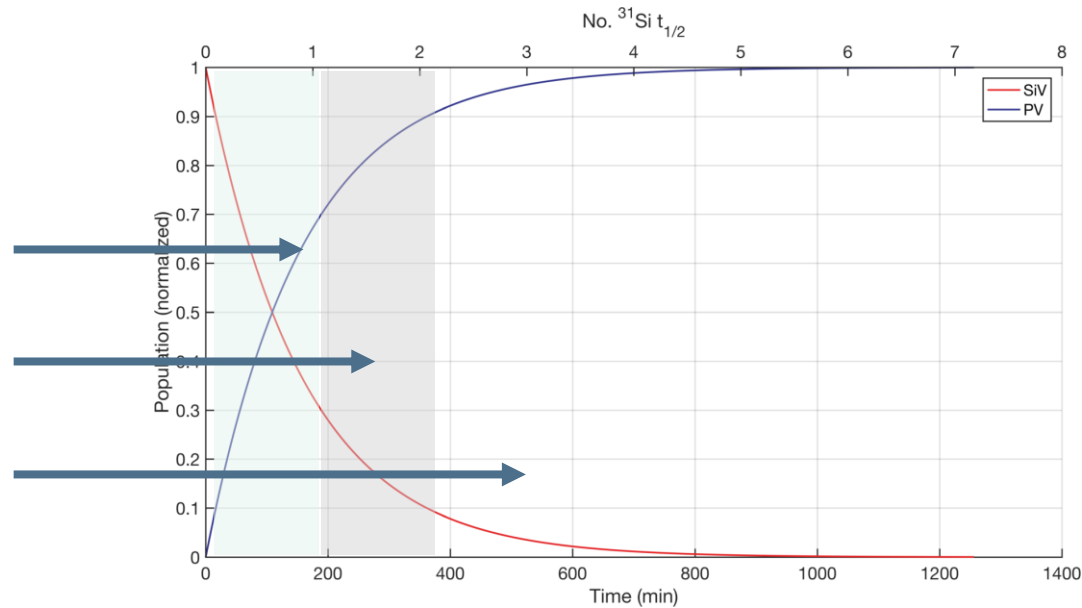
Production at ISOLDE



Implant

Anneal

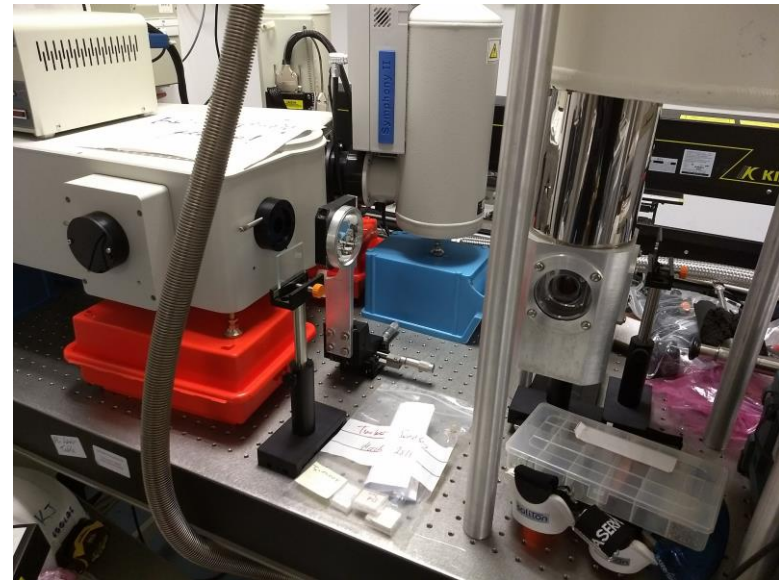
Measure



Time	No. $^{31}\text{Si } t_{1/2}$	Stage	Notes
00:00	0	Implantation of ^{31}Al	Decays to Si with $t_{1/2} < 1 \text{ s}$
02:30	1.0	Insertion into furnace	Furnace at 850°C
04:30	1.7	Removal from furnace	
05:00	1.9	Insertion into cryostat	Cryostat pre-cooled to 100 K
05:30	2.1	PL measurements begin	

Measurement at ISOLDE

- ▶ Close proximity of implantation beam and measurement enables rapid turnaround
 - Measurements start at $\sim 2 t_{1/2}$
 - Matrix of doses (single to ensemble)
- ▶ Modular PL system
 - Simple to add additional excitation
- ▶ Wide detection window
 - High efficiency detection 350-1700 nm
- Conditions at ISOLDE are unique for maximising the probability of detecting PV^x



Charge state control

▶ Problem:

- substitutional phosphorus in diamond is a donor (~0.6 eV)
- PV is predicted to be a deep acceptor [1]
- ➔ Hard to stabilize neutral and positive charge states of PV:



▶ Solution:

- charge state control through doping and surface termination
- ➔ Light ($\sim 10^{17} \text{ cm}^{-3}$) B-doping → p-type
- ➔ Ultrapure ($< 10^{13} \text{ cm}^{-3}$ impurities) material → intrinsic
- ➔ Samples to be supplied at zero cost by the Quantum Technologies group at Element Six Ltd.



Conclusion

Primary goal:

- ▶ Identification and optical / spin characterization of PV^x in diamond

Approach:

- ▶ Use rapid turnaround, high-efficiency measurements at ISOLDE to maximise the chance of detecting transient decay of



- ▶ Use offline time between first and second requested runs to:
 - feedback from original measurements and optimize second run
 - perform additional experiments at Warwick e.g. confocal microscopy, optically detected magnetic resonance

